

**FEATURES**

- Square Active Area
- Ideal for 190-400 nm Detection
- 100% Internal QE
- Excellent UV Response
- Protective Cover Plate<sup>2</sup>

**Electro-Optical Characteristics at 25 °C**

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	10 mm x 10 mm		100		mm <sup>2</sup>
Responsivity	@ 254 nm	0.08	0.09		A/W
Shunt Resistance	@ ± 10 mV	20			MOhms
Reverse Breakdown Voltage, V <sub>R</sub>	I <sub>R</sub> = 1 μA	5	10		Volts
Capacitance, C	V <sub>R</sub> = 0 V		1	3	nF
Response Time	RL = 50 Ω, V <sub>R</sub> = 10 V			10	usec

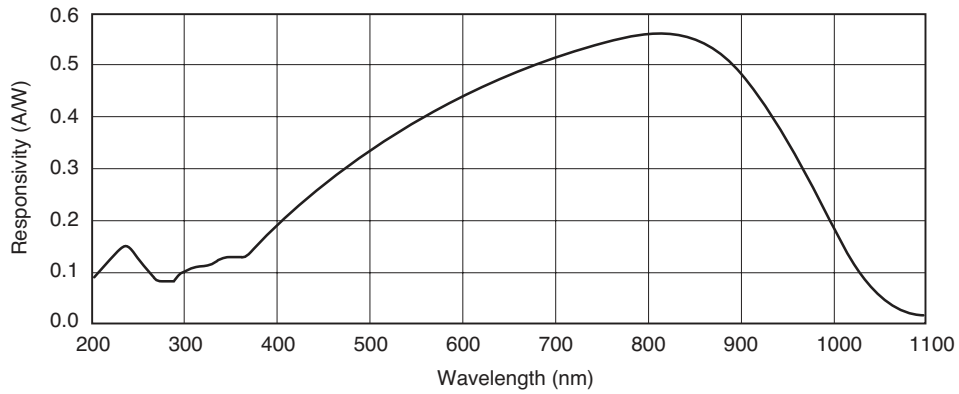
**Thermal Parameters**

Storage and Operating Temperature Range	Units
Storage Temperature Range	-20° to 100°C
Operating Temperature Range	-20° to 80°C
Lead Soldering Temperature <sup>1</sup>	240°C

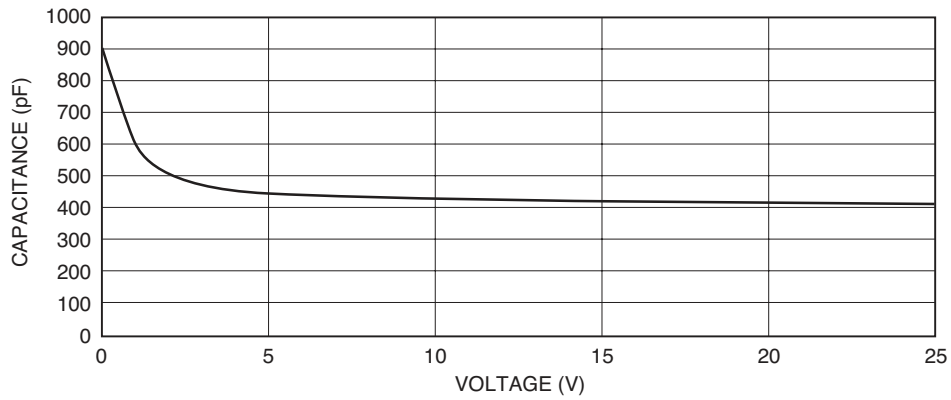
<sup>1</sup>0.08" from case for 10 seconds.

<sup>2</sup>Shipped with temporary cover to protect the photodiode and wire bonds.  
 Review the Application Note, "Handling Precautions for AXUV, SXUV, and UVG Detectors", prior to removing cover.

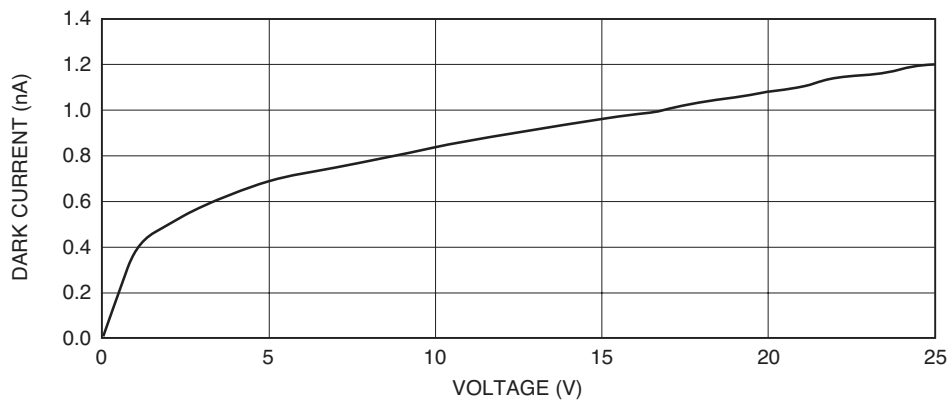
**Typical Photon Responsivity**



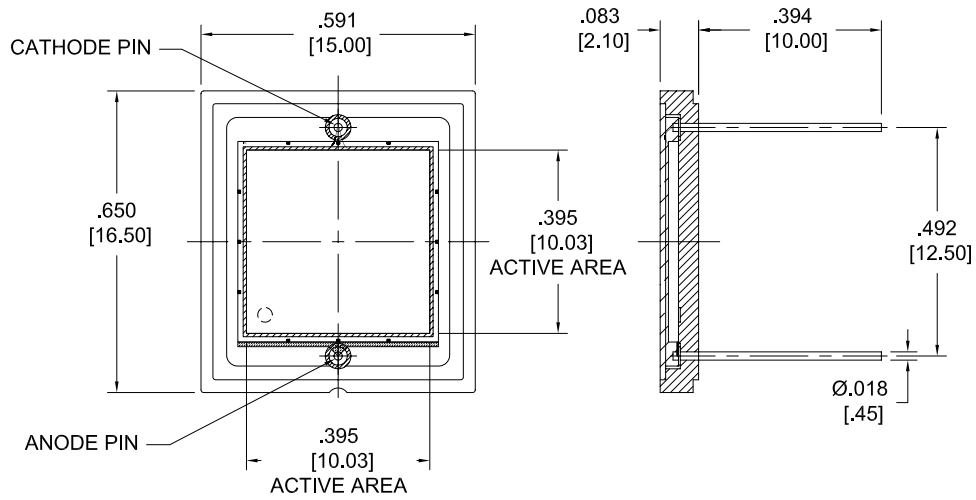
**Capacitance vs. Voltage**



**Dark Current vs. Voltage**



**Package Information**



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.